

SOT-23 Formed SMD Package

BAT54

SCHOTTKY BARRIER DIODE

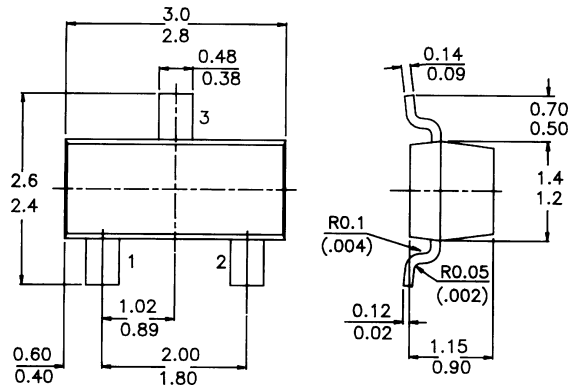
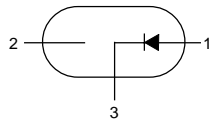
BAT54 single diode

Marking
BAT54 -4L

PACKAGE OUTLINE DETAILS
ALL DIMENSIONS IN mm

Pin configuration

- 1 = ANODE
- 2 = NC
- 3 = CATHODE



ABSOLUTE MAXIMUM RATINGS

Continuous reverse voltage	V_R	max.	30 V
Forward current	I_F	max.	200 mA
Forward voltage at $I_F = 10$ mA	V_F	<	400 mV
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	230 mW
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ; measured at $I_R = 1$ mA	t_{rr}	<	5 ns
Junction temperature	T_j	max.	125 °C

RATINGS (at $T_A = 25$ °C unless otherwise specified)

Continuous reverse voltage	V_R	max.	30 V
Forward current (DC)	I_F	max.	200 mA
Forward voltage at $I_F = 10$ mA	V_F	<	400 mV
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ; measured at $I_R = 1$ mA	t_{rr}	<	5 ns
Junction temperature	T_j	max.	125 °C

BAT54

Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	230 mW
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$
Junction temperature	T_j	max.	125 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient; mounted on a ceramic substrate of 10 mm × 8 mm × 0.6 mm

$R_{th\ j-a}$	=	430 K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Forward voltage

$I_F = 0.1\text{ mA}$	V_F	ε	240 mV
$I_F = 1\text{ mA}^*$	V_F	ε	320 mV
$I_F = 10\text{ mA}$	V_F	ε	400 mV
$I_F = 30\text{ mA}^*$	V_F	ε	500 mV
$I_F = 100\text{ mA}$	V_F	=	500 mV
	V_F	ε	1000 mV

Reverse current

$V_R = 25\text{ V}$	I_R	ε	2 μA
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Reverse breakdown voltage

$V_{(BR)R}$	>	30 V
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Diode capacitance

$V_R = 1\text{ V}; f = 1\text{ MHz}$	C_d	ε	15 pF
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Reverse recovery time when switched from

$I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}; R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$	t_{rr}	ε	5 ns
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* Temperature coefficient of forward voltage:

- 0.6 %K at $I_F = 1\text{ mA}$
- 0.3 %K at $I_F = 30\text{ mA}$

Disclaimer

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